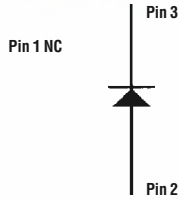




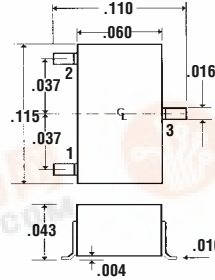
Data Sheet

200 mW EPITAXIAL PLANAR DIODES

Description



Mechanical Dimensions



FMBBAS19...21

Features

- PLANAR PROCESS
- 200 mW POWER DISSIPATION
- INDUSTRY STANDARD SOT-23 PACKAGE
- MEETS UL SPECIFICATION 94V-0

Electrical Characteristics @ 25°C.	FMBBAS19...21			Units
Maximum Ratings	FMBBAS19	FMBBAS20	FMBBAS21	
Peak Reverse Voltage... V_{RM}	120	200	250	Volts
RMS Reverse Voltage... $V_{R(rms)}$	100	150	200	Volts
Average Forward Rectified Current... I_O		625		mAmps
Non-Repetitive Peak Forward Surge Current... I_{FSM}		2.5		Amps
Forward Voltage... V_F @ $I_F = 100$ mA		1.0		Volts
DC Reverse Current... I_R @ $V_R = 70V$		0.1		μAmps
Power Dissipation... P_D		200		mW
Reverse Recovery Time... t_{RR}		50		nS
Operating Temperature Range... T_J		-25 to 85		°C
Storage Temperature Range... T_{STRG}		-65 to 150		

°C

Device Under Test

